恒光发
HENG GUANG FA

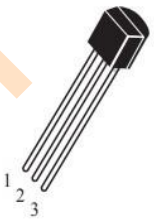
NPN Silicon Transistor

SS8050

FEATURES

- **Complementary to SS8550**
- **Package:TO-92,SOT-23**

TO-92



1. EMITTER
2. BASE
3. COLLECTOR

SOT-23



1. BASE
2. EMITTER
3. COLLECTOR

Maximum Ratings (Ta = 25°)

Parameter	Symbol	Rating		Unit
Collector-base voltage	BV_{CBO}	40		V
Collector-emitter voltage	BV_{CEO}	25		V
Emitter-base voltage	BV_{EBO}	5		V
Collector current	I_{CM}	1.5		A
Collector Power Dissipation	P_C	SOT-23	0.3	W
		TO-92	1	
Junction Temperature	Tj	150		℃
Storage Temperature	Tstg	-55～＋150		℃

Electrical Characteristics（Ta=25℃）

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Collector-Base Breakdown Voltage	BV_{CBO}	I_C=100μA，I_E=0	40			V
Collector-Emitter Breakdown Voltage	BV_{CEO}	I_C=1mA，I_B=0	25			V
Emitter-Base Breakdown Voltage	BV_{EBO}	I_E=100μA，I_C=0	5			V
collector-base cut-off current	I_{CBO}	V_{CB}=40V，I_E=0			0.1	μA
collector-emitter cut-off current	I_{CEO}	V_{CE}=20V，I_B=0			0.1	μA
emitter-base cut-off current	I_{EBO}	V_{EB}=5V，I_C=0			0.1	μA
DC current gain	H_{FE}	V_{CE}=1V，I_C=100mA	85		400	
		V_{CE}=1V，I_C=800mA	40			
collector-emitter saturation voltage	V_{CESAT}	I_C=800mA，I_B=80mA			0.5	V
Base-Emitter Saturation Voltage	V_{BESAT}	I_C=800mA，I_B=80mA			1.2	
Transition frequency	f_T	V_{CE}=10V，I_C=50 mA	100			MH_Z

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